TOSHIBA TA8312F

TENTATIVE

TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MULTI CHIP

TA8312F

MOTOR DRIVER FOR CAMERA

TA8312F is Multi Chip IC incorporates 6 low saturation discrete transistors which equipped bias resistor and Free-Wheeling diode.

This IC is suitable for a camera use motor drive applications.

FEATURES

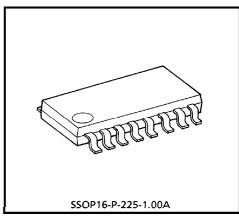
• Suitable for high efficiency motor drive circuit.

• Built-in Bias Resistor : $R = 10k\Omega$

Built-in Free-Wheeling diode

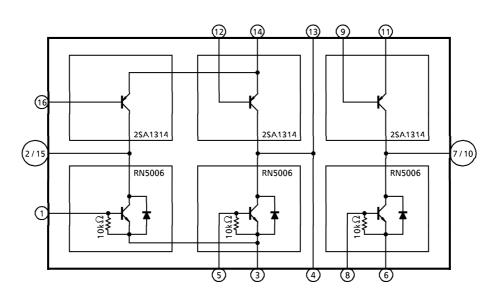
Small package sealed : SSOP16

Low saturation voltage



Weight: 0.14g (Typ.)

BLOCK DIAGRAM



980910EBA2

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _C C	10	V
	VCBO	10	V
Breakdown Voltage	VCEO	10	V
	V _{EBO}	6	V
Output Current	IOUT	2	Α
Base Current	ΙB	0.4	Α
Power Dissipation	P _D	330	mW
Junction Temperature	Tj	150	°C
Operating Temperature	T _{opr}	- 20~60	°C
Storage Temperature	T _{stg}	- 55∼150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	MEASURING Tr	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Gain	h _{FE} 1	2SA1314	_	$V_{CE} = -1V, I_{C} = -0.5A$	140	_	600	
	h _{FE 2}	RN5006	_	$V_{CE} = 1V, I_{C} = 0.5A$	160	_	600	
Saturation	V _{CE} 1	2SA1314	_	$I_C = -2A$, $I_B = -50mA$	- 0.5	_	_	٧
Voltage	V _{CE 2}	RN5006	_	$I_C = 2A$, $I_B = 50mA$	_	_	0.5	٧
Output Leak Current	lOFF		_	V _{CC} = 7V	_	_	1.0	μΑ
Input Resistance	R	RN5006	_		7	10	13	kΩ
Diode Forward Voltage	V _F	RN5006	_	I _F = 300mA	_	0.89	1.2	V
Transition	f _{T1}	2SA1314	_	$V_{CE} = -1V$, $I_{C} = -0.5A$	_	140	_	MHz
Frequency	f _{T2}	RN5006	_	$V_{CE} = 1V, I_{C} = 0.5A$	_	140	_	MHz

980910EBA2'

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OUTLINE DRAWING SSOP16-P-225-1.00A Unit : mm 0.6TYP 8.7MAX 8.2±0.2 0.525±0.2

Weight: 0.14g (Typ.)